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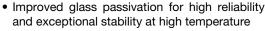
## Vishay Semiconductors

# Medium Power Phase Control Thyristors (Stud Version), 22 A



PRIMARY CHARACTERISTICS					
I <sub>T(AV)</sub>	22 A				
V <sub>DRM</sub> /V <sub>RRM</sub>	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V				
$V_{TM}$	1.70 V				
I <sub>GT</sub>	60 mA				
T <sub>J</sub>	-65 °C to +125 °C				
Package	TO-48 (TO-208AA)				
Circuit configuration	Single SCR				

#### **FEATURES**





- High dl/dt and dV/dt capabilities
- Standard package
- · Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V<sub>DRM</sub>/V<sub>RRM</sub>
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

#### **TYPICAL APPLICATIONS**

- Medium power switching
- · Phase control applications

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		22	Α		
$I_{T(AV)}$	T <sub>C</sub>	85	°C		
I <sub>T(RMS)</sub>		35	Α		
I <sub>TSM</sub>	50 Hz	400	۸		
	60 Hz	420	A		
l <sup>2</sup> t	50 Hz	793	— A <sup>2</sup> s		
	60 Hz	724	A-s		
V <sub>DRM</sub> /V <sub>RRM</sub>		100 to 1200	V		
tq	Typical	110	μs		
T <sub>J</sub>		-65 to +125	°C		

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V <sub>DRM</sub> /V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE <sup>(1)</sup> V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK VOLTAGE <sup>(2)</sup> V	$I_{DRM}/I_{RRM}$ MAXIMUM AT $T_J = T_J$ MAXIMUM mA			
	10	100	150	20			
	20	200	300				
	40	400	500				
VS-22RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

#### **Notes**

(1) Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

<sup>(2)</sup> For voltage pulses with  $t_p \le 5$  ms



PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS	
Maximum average on-state current	,	100° sinus	oidal conduction		22	A °C
at case temperature	I <sub>T(AV)</sub>	160 Sinusc	dai conduction		85	
Maximum RMS on-state current	I <sub>T(RMS)</sub>				35	Α
		t = 10 ms	No voltage		400	
Maximum peak, one-cycle		t = 8.3 ms	reapplied		420	A
non-repetitive surge current	I <sub>TSM</sub>	t = 10 ms	100 % V <sub>RRM</sub>		335	_ A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	355	
Maximum I <sup>2</sup> t for fusing		t = 10 ms	No voltage	No voltage reapplied  100 % V <sub>RRM</sub> reapplied	793	- A <sup>2</sup> s
	l <sup>2</sup> t	t = 8.3 ms	reapplied		724	
		t = 10 ms	100 % V <sub>RRM</sub>		560	
		t = 8.3 ms	reapplied		515	
Maximum $I^2 \sqrt{t}$ for fusing	I <sup>2</sup> √t	$t = 0.1$ to 10 ms, no voltage reapplied, $T_J = T_J$ maximum		7930	A²√s	
Low level value of threshold voltage	V <sub>T(TO)1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		0.83	V	
High level value of threshold voltage	V <sub>T(TO)2</sub>	$(I > \pi \times I_{T(AV)})$	$f_0$ ), $T_J = T_J$ maxim	ium	0.95	V
Low level value of on-state slope resistance	r <sub>t1</sub>	(16.7 % x $\pi$ x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$ ), $T_J = T_J$ maximum		14.9	0	
High level value of on-state slope resistance	r <sub>t2</sub>	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		13.4	mΩ	
Maximum on-state voltage	$V_{TM}$	I <sub>pk</sub> = 70 A, T <sub>J</sub> = 25 °C		1.70	V	
Maximum holding current	I <sub>H</sub>	T _ 05 °C	anada aunnis 6	V registive lead	130	
Latching current	ΙL	1 J = 25 °C,	$T_J = 25$ °C, anode supply 6 V, resistive load		200	mA

SWITCHING							
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS		
	$V_{DRM} \le 600 \text{ V}$						A/μs
Maximum rate of rise	$V_{DRM} \le 800 \text{ V}$	dl/dt	$T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$ Gate pulse = 20 V, 15 $\Omega$ , $t_D = 6 \mu s$ , $t_r = 0.1 \mu s$ maximum	180			
of turned-on current	$V_{DRM} \le 1000 \text{ V}$		$I_{TM} = (2 \text{ x rated dI/dt}) \text{ A}$	160			
	$V_{DRM} \le 1600 \text{ V}$			150			
Typical turn-on time		t <sub>gt</sub>	$T_J = 25$ °C, at rated $V_{DRM}/V_{RRM}$ , $T_J = 125$ °C	0.9			
Typical reverse recovery time		t <sub>rr</sub>	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$ , $t_p > 200 \ \mu s$ , $dI/dt = -10 \ A/\mu s$	4	μs		
Typical turn-off time		t <sub>q</sub>	$T_J=T_J$ maximum, $I_{TM}=I_{T(AV)},t_p>200~\mu s,V_R=100~V,dI/dt=$ - 10 A/µs, dV/dt = 20 V/µs linear to 67 % $V_{DRM},$ gate bias 0 V to 100 W	110	μ		

#### Note

•  $t_q = 10 \mu s$  up to 600 V,  $t_q = 30 \mu s$  up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	T <sub>J</sub> = T <sub>J</sub> maximum linear to 100 % rated V <sub>DRM</sub>	100	V/µs
of off-state voltage	uv/ut	T <sub>J</sub> = T <sub>J</sub> maximum linear to 67 % rated V <sub>DRM</sub>	300 (1)	ν/μδ

#### Note

(1) Available with:  $dV/dt = 1000 V/\mu s$ , to complete code add S90 i.e. 22RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TES	T CONDITIONS	VALUES	UNITS
Maximum peak gate power	$P_{GM}$	$T_{.1} = T_{.1}$ maximum		8.0	W
Maximum average gate power	P <sub>G(AV)</sub>	I J = I J Maximum		2.0	VV
Maximum peak positive gate current	I <sub>GM</sub>	T <sub>J</sub> = T <sub>J</sub> maximum		1.5	Α
Maximum peak negative gate voltage	-V <sub>GM</sub>	$T_J = T_J$ maximum		10	V
		T <sub>J</sub> = - 65 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units	90	
DC gate current required to trigger	I <sub>GT</sub>	T <sub>J</sub> = 25 °C		60	mA
		T <sub>J</sub> = 125 °C		35	
	V <sub>GT</sub>	T <sub>J</sub> = - 65 °C		3.0	V
DC gate voltage required to trigger		T <sub>J</sub> = 25 °C	6 V anode to cathode applied	2.0	
		T <sub>J</sub> = 125 °C		1.0	
DC gate current not to trigger	$I_{GD}$	T <sub>J</sub> = T <sub>J</sub> maximum, V <sub>DRM</sub> = Rated value		2.0	mA
DC gate voltage not to trigger	V <sub>GD</sub>	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V <sub>DRM</sub> anode to cathode applied	0.2	٧

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VAL	VALUES	
Maximum operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65 to +125		°C
Maximum thermal resistance, junction to case	R <sub>thJC</sub>	DC operation 0.86		14004	
Maximum thermal resistance, case to heat sink	R <sub>thCS</sub>	Mounting surface, smooth, flat and greased 0.35		35	K/W
			TO NUT	TO DEVICE	
			20 (27.5)	25	lbf ⋅ in
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf · m
		(Non labilitation timedae)		2.8	N · m
Approximate weight			1	4	g
			0.	49	OZ.
Case style		See dimensions - link at the end of datasheet	t TO-48 (TO-208AA)		AA)

△R <sub>thJC</sub> CONDUCTION	I			
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.21	0.15		
120°	0.25	0.25		
90°	0.31	0.34	$T_J = T_J$ maximum	K/W
60°	0.45	0.47		
30°	0.76	0.76		

### Note

• The table above shows the increment of thermal resistance RthJC when devices operate at different conduction angles than DC

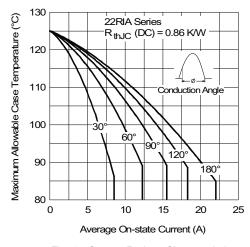


Fig. 1 - Current Ratings Characteristics

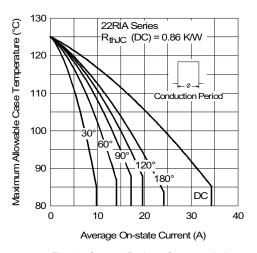


Fig. 1 - Current Ratings Characteristics

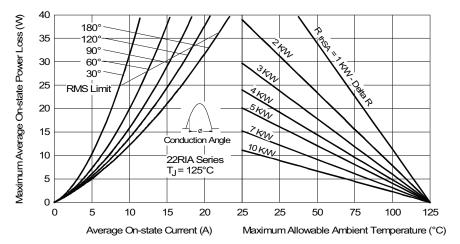


Fig. 2 - On-State Power Loss Characteristics

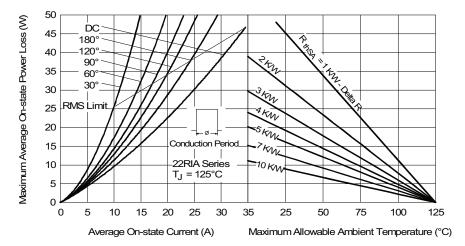


Fig. 3 - On-State Power Loss Characteristics

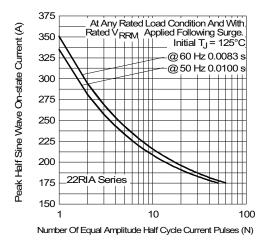


Fig. 4 - Maximum Non-Repetitive Surge Current

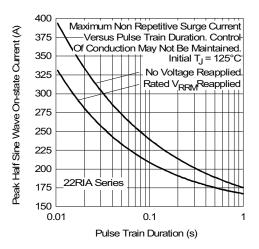


Fig. 5 - Maximum Non-Repetitive Surge Current

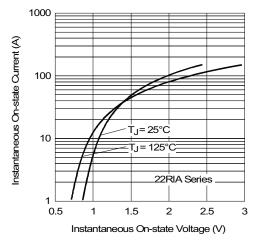


Fig. 6 - Forward Voltage Drop Characteristics

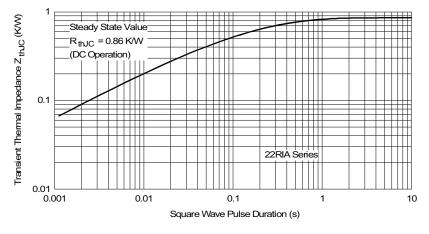


Fig. 7 - Thermal Impedance  $Z_{thJC}$  Characteristics

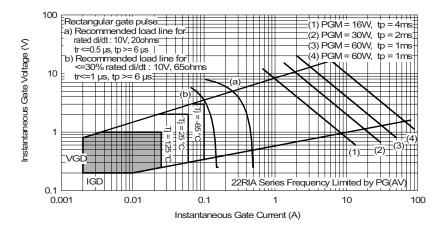
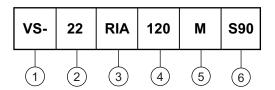


Fig. 8 - Gate Characteristics

#### **ORDERING INFORMATION TABLE**

Device code



1 - Vishay Semiconductors product

2 - Current code

3 - Essential part number

Voltage code x 10 = V<sub>RRM</sub> (see Voltage Ratings table)

5 - None = stud base TO-48 (TO-208AA) 1/4" 28UNF-2A

M = stud base TO-48 (TO-208AA) M6 x 1

6 - Critical dV/dt:

None = 300 V/µs (standard value)

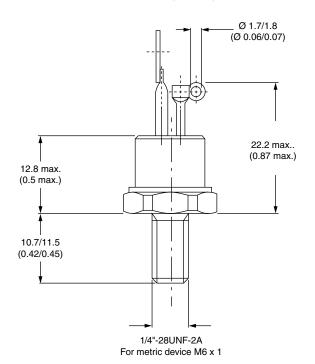
S90 = 1000 V/µs (special selection)

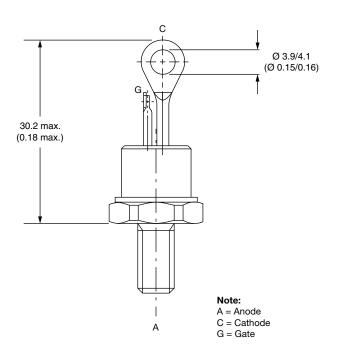
LINKS TO RELAT	TED DOCUMENTS
Dimensions	www.vishay.com/doc?95333

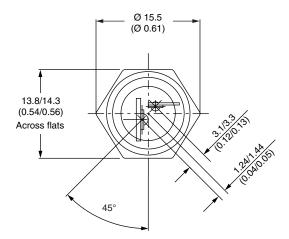


# TO-208AA (TO-48)

## **DIMENSIONS** in millimeters (inches)









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